

neBEM

Recent Developments and Applications

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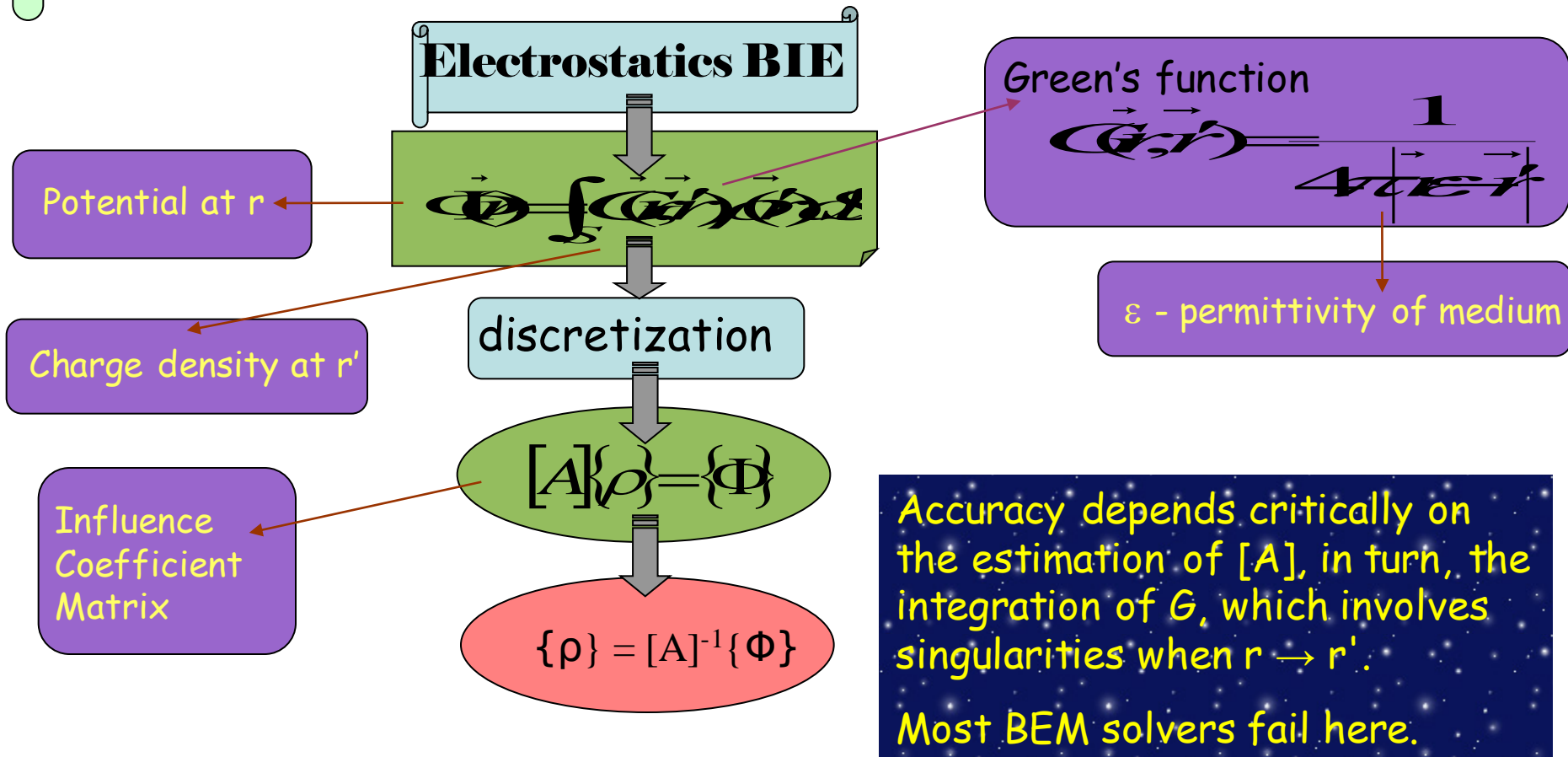
Outline

- *Numerical adventures:* Taming stubborn system of equations
- *Applications as a component of the simulation framework:* RPC, Micromegas, GEM, MHSP
- *Future plans:*

Numerical Adventures

BEM Solvers

- Numerical implementation of boundary integral equations (BIE) based on Green's function by discretization of boundary.
- Boundary elements endowed with distribution of sources, doublets, dipoles, vortices (singularities).
- Useful in fluid dynamics, fracture mechanics, acoustics, optics, gravitation, electromagnetics, quantum mechanics ...



nearly exact BEM

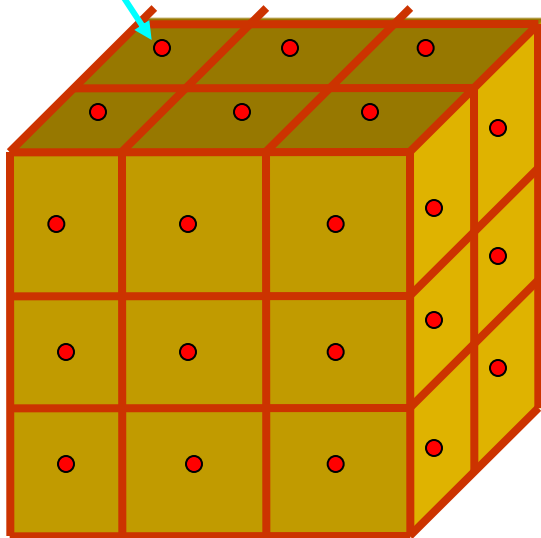
Centroid Collocation

Basis Function Approach

$$\psi(x_i) = \sum_{j=1}^n \alpha_j \int_{\Gamma} \frac{1}{\|x_i - x\|} d\mathbf{x} = A_{ij}$$

x_{c_i} Collocation point

Node where only boundary condition is satisfied



Carry out the integrations!

$$A_{ij} = \int_{\Gamma} G(x_i, x) \phi_j(x) d\mathbf{x}$$

$$\begin{bmatrix} A_{11} & \dots & \dots & \dots & A_{1n} \\ \vdots & & & & \vdots \\ \vdots & & & & \vdots \\ A_{n1} & \dots & \dots & \dots & A_{nn} \end{bmatrix} \begin{bmatrix} \alpha_1 \\ \vdots \\ \alpha_n \end{bmatrix} = \begin{bmatrix} \psi(x_{c_1}) \\ \vdots \\ \psi(x_{c_n}) \end{bmatrix}$$

No singularities, no special treatments, no additional formulations

System of algebraic equations

Important definitions

The **Singular Values** of the rectangular / square matrix A with real elements is defined as the square root of the eigenvalues of $A^T A$.

The **Condition Number** is the ratio of the largest to the smallest singular value.

A matrix is **Ill-Conditioned** Matrix if the condition number is too large. How large the condition number can be, before the matrix is ill-conditioned, is determined by the machine precision. Well-conditioned matrices have condition numbers close to 1.

A matrix is **Singular** if the condition number is infinite. The determinant of a singular matrix is zero.

The **Rank** of a matrix, is the dimension of the range of the matrix. This corresponds to the number of non-singular values for the matrix, i.e. the number of linear independent rows of the matrix.

Why need we be concerned?

Encounters of strange kind

A square matrix A is ill-conditioned if it is invertible but can become non-invertible (singular) if some of its entries are changed ever so slightly.

Solving linear systems whose coefficient matrices are ill-conditioned is tricky also because even a small change in the right-hand side vector can lead to radically different answers.

In presence of round-off errors, ill-conditioned matrices are very hard to handle.

They occur when degenerate boundaries, degenerate scales related to special geometries, mixed boundary conditions, large difference in dielectric permittivity are present.

Besides unit circle, the degenerate scale problem under different contours with specific geometry may be encountered, and the accurate degenerate scale is dependent on the discretization boundary density in BEM. Mathematically speaking, the singularity pattern distributed along a ring boundary resulting in a zero field introduces a degenerate scale.

Good old days

LU decomposition

$$\begin{bmatrix} \alpha_{11} & 0 & 0 & 0 \\ \alpha_{21} & \alpha_{22} & 0 & 0 \\ \alpha_{31} & \alpha_{32} & \alpha_{33} & 0 \\ \alpha_{41} & \alpha_{42} & \alpha_{43} & \alpha_{44} \end{bmatrix} \cdot \begin{bmatrix} \beta_{11} & \beta_{12} & \beta_{13} & \beta_{14} \\ 0 & \beta_{22} & \beta_{23} & \beta_{24} \\ 0 & 0 & \beta_{33} & \beta_{34} \\ 0 & 0 & 0 & \beta_{44} \end{bmatrix} = \begin{bmatrix} a_{11} & a_{12} & a_{13} & a_{14} \\ a_{21} & a_{22} & a_{23} & a_{24} \\ a_{31} & a_{32} & a_{33} & a_{34} \\ a_{41} & a_{42} & a_{43} & a_{44} \end{bmatrix}$$

$$\alpha_{ii} = \mathbf{1}$$

The LU decomposition is a method reducing a square matrix to a product of two triangular matrices (lower triangular and upper triangular). It does not require a positive definite matrix, but there is no guarantee that it is equivalent to solving a system of linear equations by the Gauss elimination. Its **advantages** include **easy implementation**, **speed** and **disadvantages** include **numerical instability without pivoting**.

The LU decomposition is most commonly used in the solution of systems of simultaneous linear equations. The method is at least twice as fast as other decomposition algorithms. Unfortunately, the method has less desirable numerical problems.

For ill-conditioned problems, or when high accuracy is needed, other decomposition would be preferred.

Enters Singular Value Decomposition

SVD of $A \in \mathbf{R}^{m \times n}$ with $\mathbf{Rank}(A) = r$:

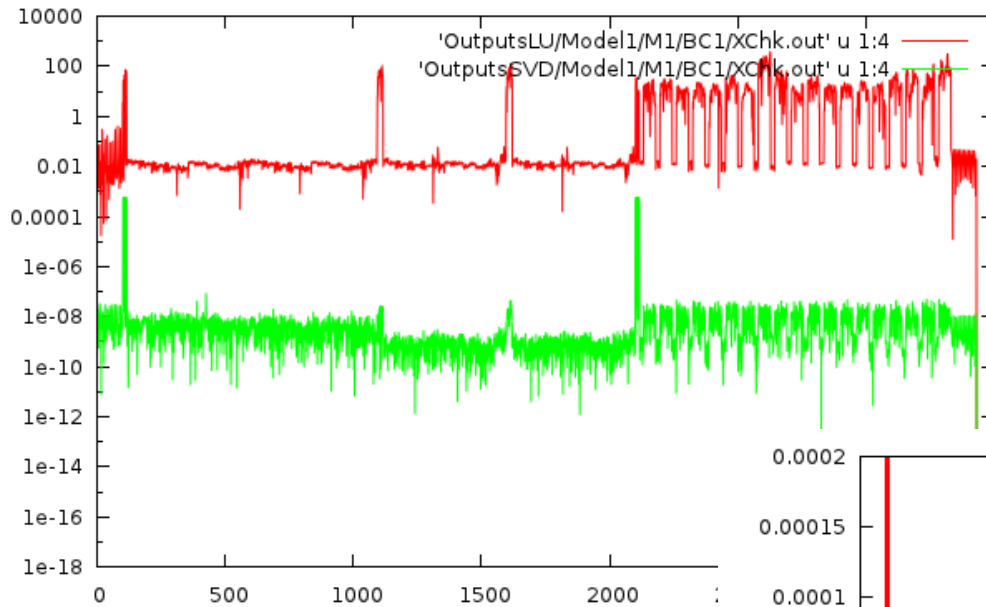
$$A = U_1 \Sigma_1 V_1^T = \begin{bmatrix} u_1 & \cdots & u_r \end{bmatrix} \begin{bmatrix} \sigma_1 & & \\ & \cdots & \\ & & \sigma_r \end{bmatrix} \begin{bmatrix} v_1^T \\ \vdots \\ v_r^T \end{bmatrix}$$

Using two orthonormal matrices, SVD can diagonalize any matrix and the results of SVD can tell a lot about (numerical) properties of the matrix. SVD offers a numerically stable way to solve a system of linear equations. The diagonal entries of Σ are the singular values of the least-squares matrix A . For N charges there will be N singular values. The condition number of A is defined by the ratio of the largest to the smallest singular value .

Thus, one can compute the eigenvalues of directly from the original matrix. Second, the number of nonzero singular values equals the rank of a matrix. Consequently, SVD can be used to find an effective rank of a matrix, to check a near singularity and to compute the condition number of a matrix. That is, it allows to assess conditioning and sensitivity to errors of a given system of equations.

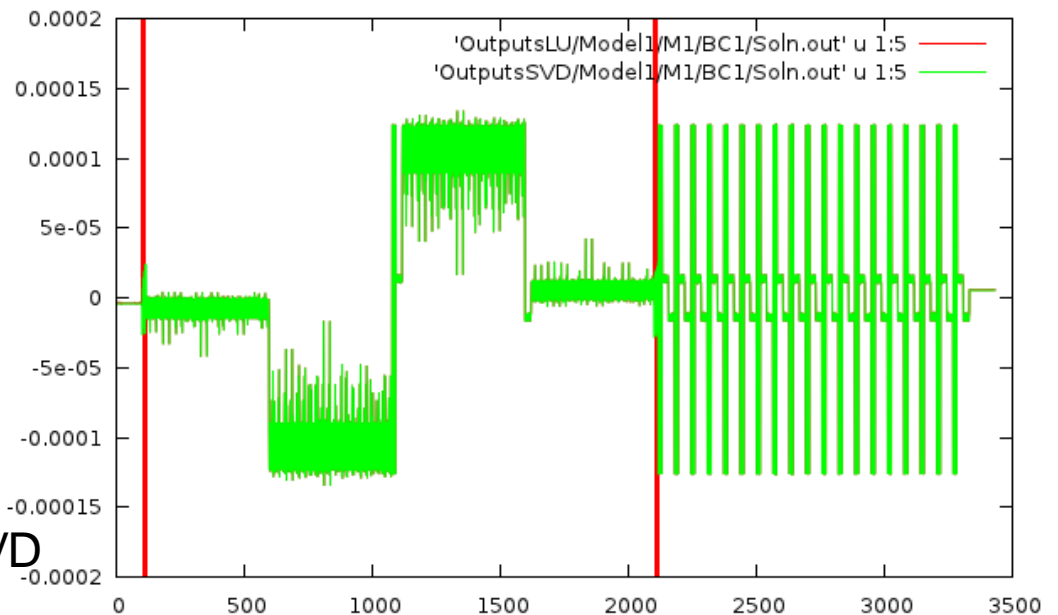
Observation of significant improvements

Error estimates



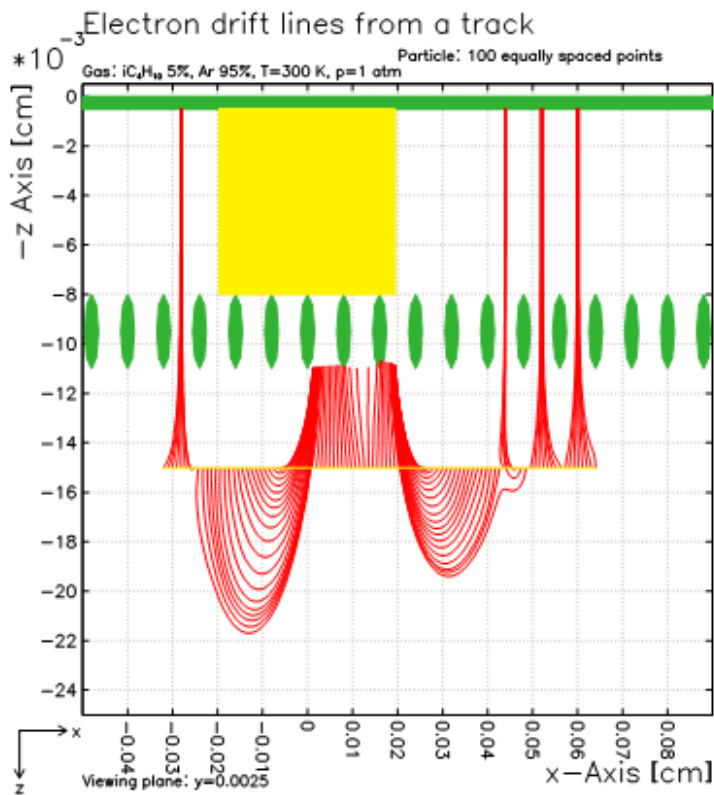
Errors using LU and SVD
(note the log scale!)

Charge densities using LU and SVD

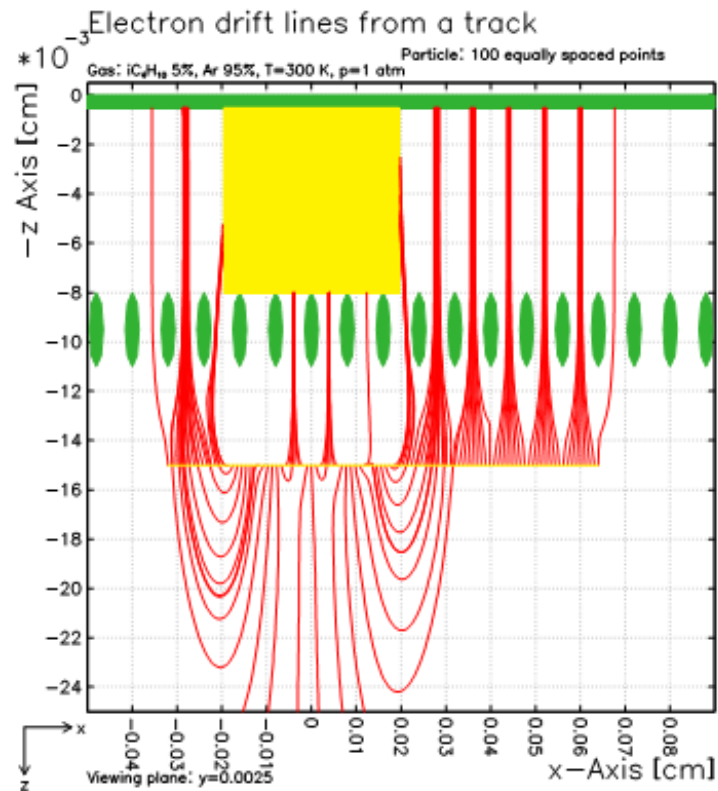


Observation of significant differences

Effect on detector physics



Drift lines in a bulk micromegas (LU)



Drift lines in a bulk micromegas (SVD)

Recent applications

neBEM Strengths

- Can handle large length scale variation, including thin structures
- Can provide potential and field at arbitrary locations
- Can handle intricate 3D geometries
- Can handle multiple-material complex systems
- **Has been made reasonably robust and fast**
- Integrated to the fortran version of Garfield
- Using its toolkit nature, neBEM can be easily interfaced

New simulation framework

Garfield+Magboltz+Heed+neBEM

neBEM (nearly exact Boundary Element Method) as a toolkit

A new formulation based on green's function that allows the use of exact close-form analytic expressions while solving 3D problems governed by Poisson's equation. It is very precise even in critical near-field regions and microscopic length scale.

It is easy to use, interface and integrate neBEM

Stand-alone

A driver routine

An interface routine

Post-processing, if necessary

Garfield

Garfield prompt

Garfield script

Interface to Magboltz, Heed

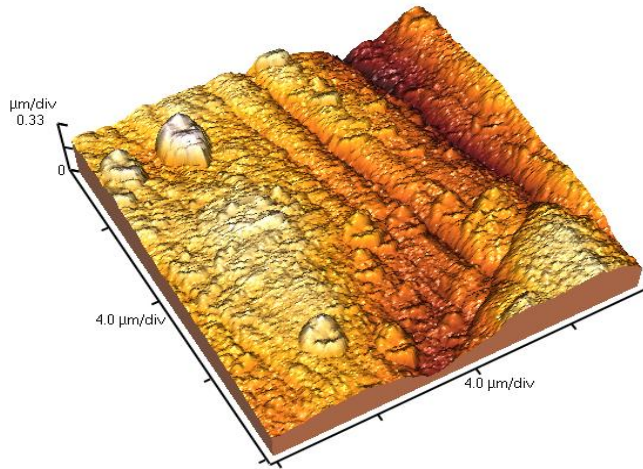
Charge density at all the interfaces

Potential at any arbitrary point

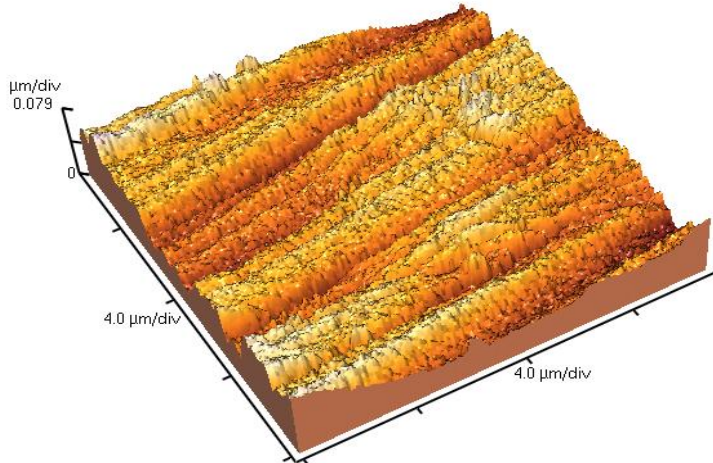
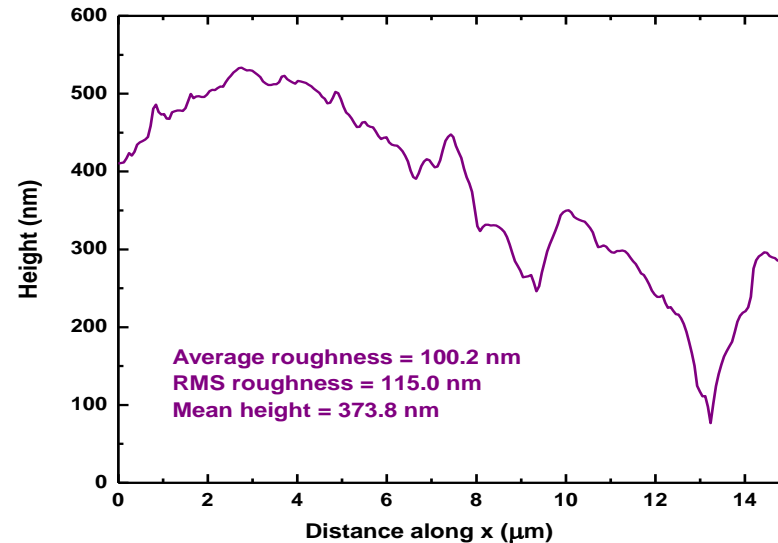
Field at any arbitrary point

Capacitance, forces on device components properties can be obtained by post-processing

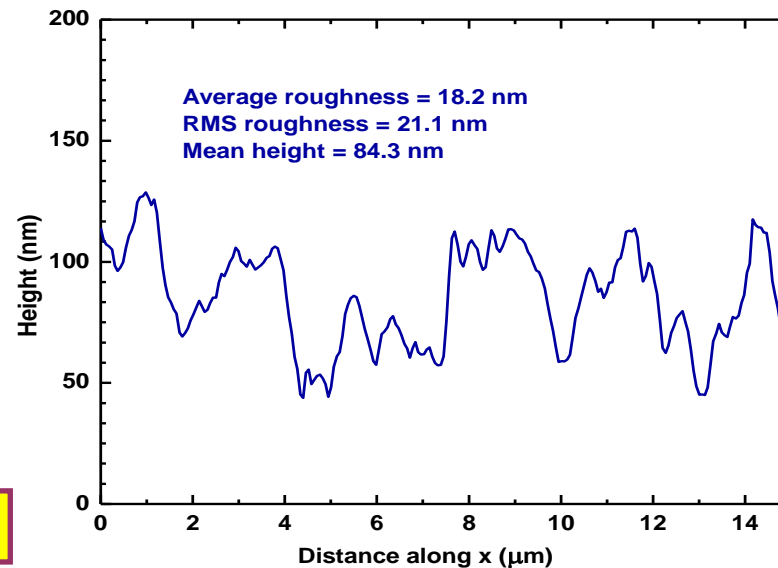
Roughness studies of RPCs



2 mm thick



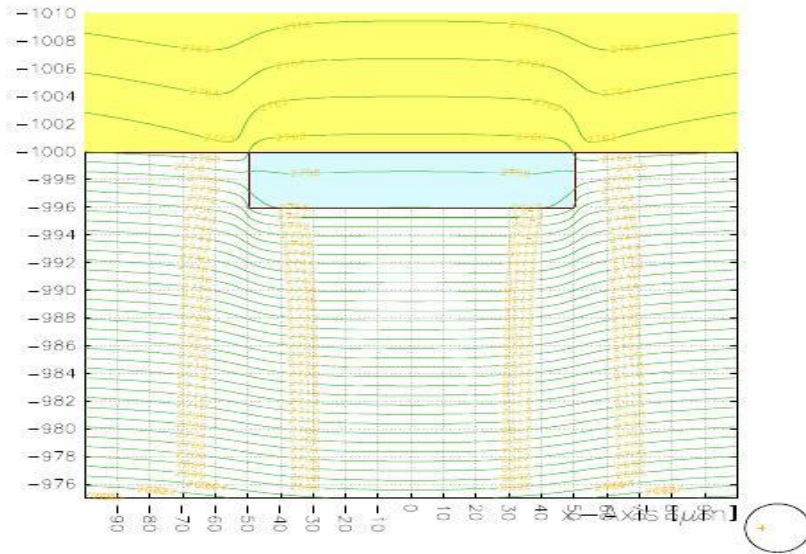
1.6 mm thick (Smoother surface)



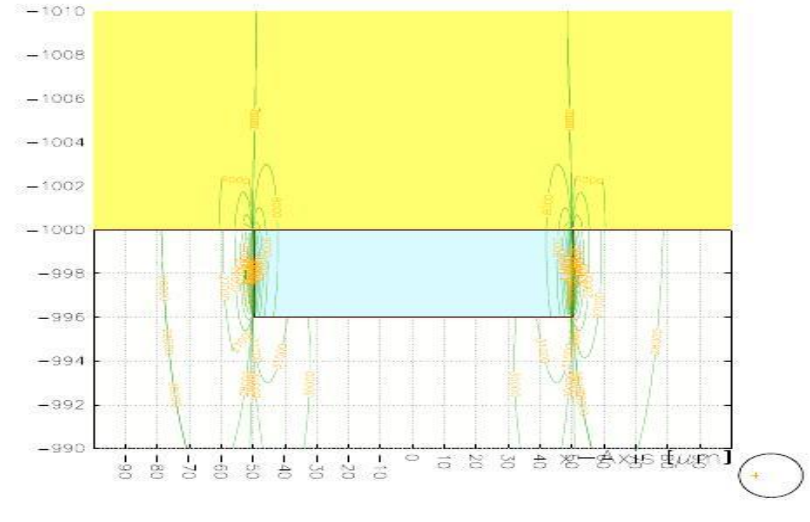
AFM Images and analysis of uncoated P-120 bakelite surfaces

Roughness studies on RPCs

Contours of V

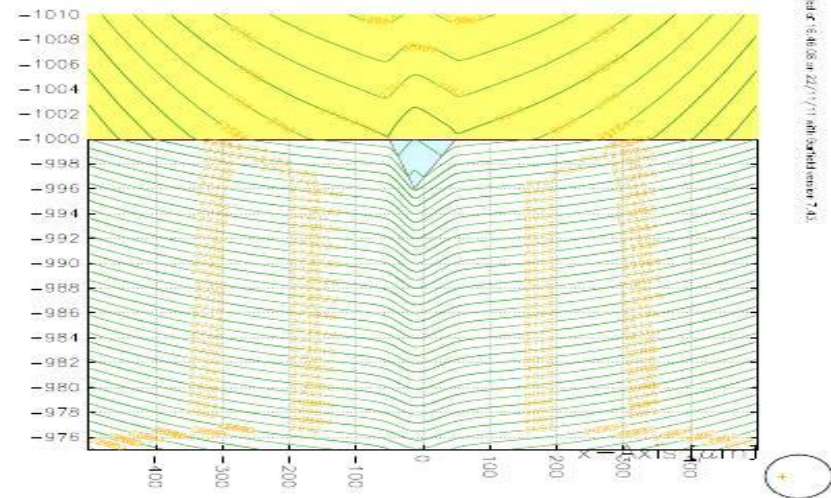


Contours of EZ



- Regularly shaped 4 micron high dielectric pillar/pyramid on bakelite surface
- Base of the rectangular pillar and the pyramid shaped one is 100 micron square
- Gas gap is 2 mm

Contours of V

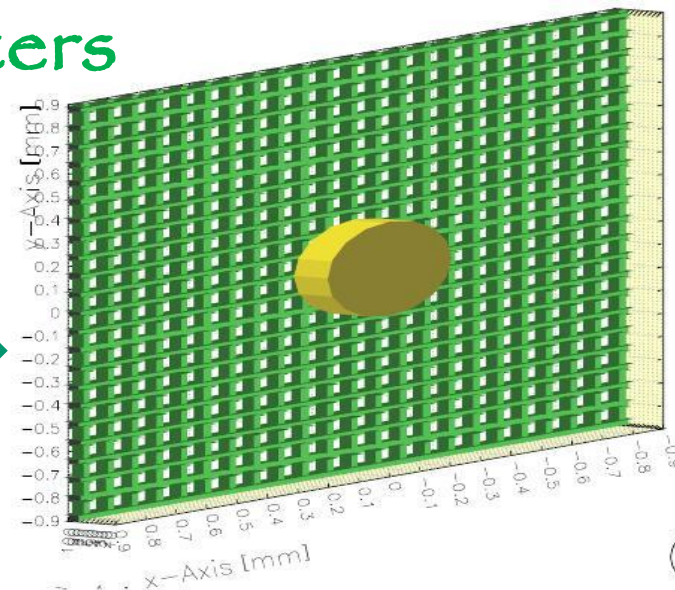


Micromegas

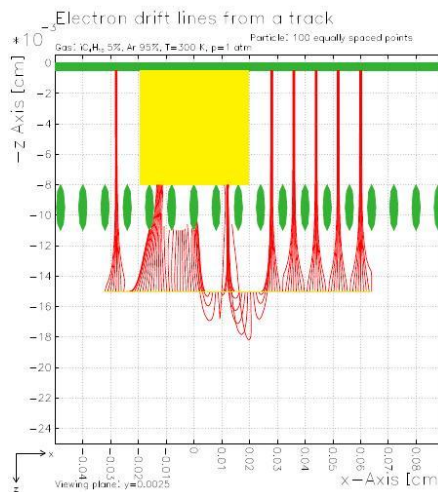
Effect of spacers

- Regularly spaced insulating pillars between grid and anode plane, guarantee the uniformity of gap
- Pillars radius larger than mesh cell size, particles are not detected in this region

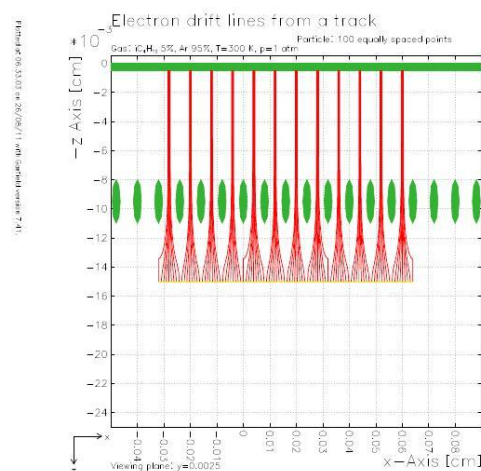
Mesh with one spacer : mesh pitch $80 \mu\text{m}$, spacer diameter $400 \mu\text{m}$



- ✓ Electron drift lines get distorted in spacer region, do not reach anode plane
- ✓ Total charge collected by anode affected
- ✓ Effect on spatial resolution, energy resolution etc.
- ✓ Only preliminary results, need further investigation



With Spacer (LU)



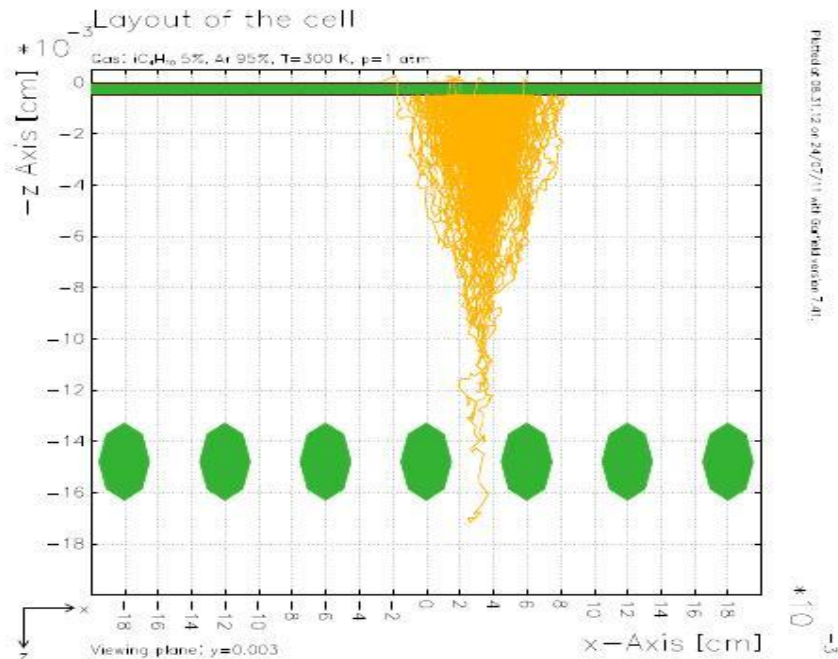
Without Spacer

Electron Drift Lines (2D Picture)

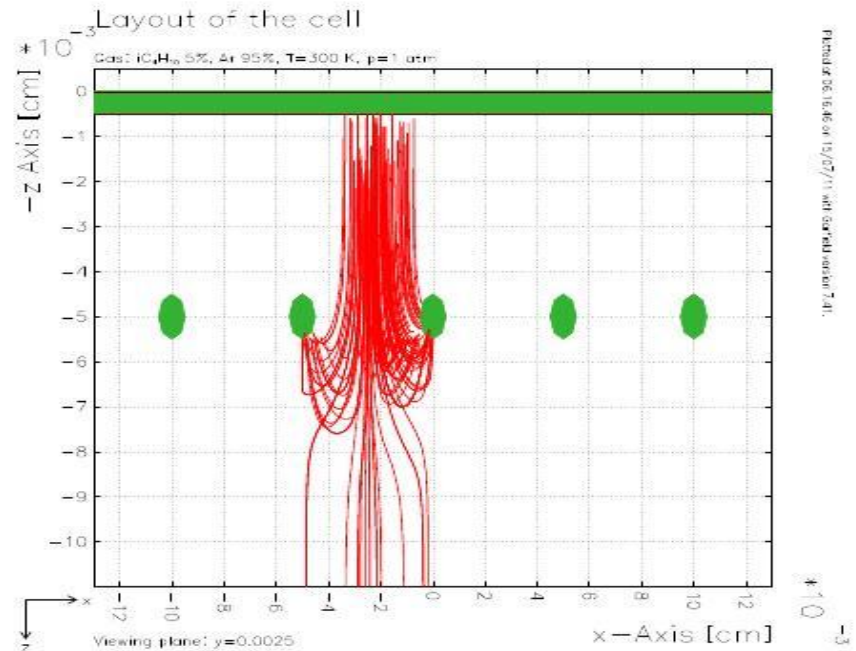


Micromegas Ion back-flow

- *Secondary ions from amplification region drift to drift region*
- *Distortion of electric field*
- *Micromegas micromesh stops a large fraction of these ions*

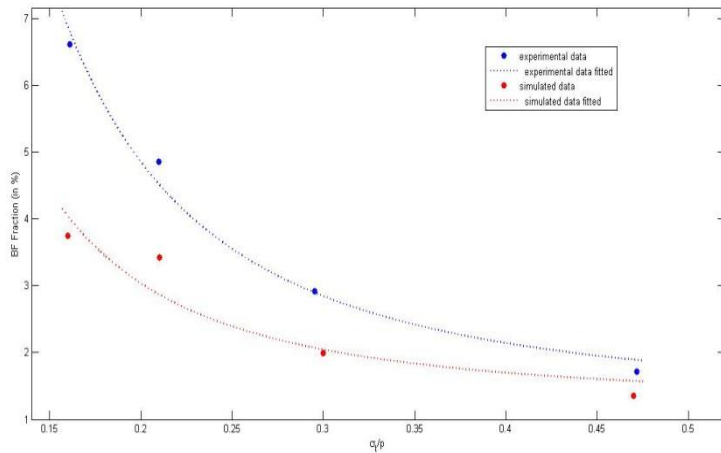


Avalanche of Electrons (2D picture)

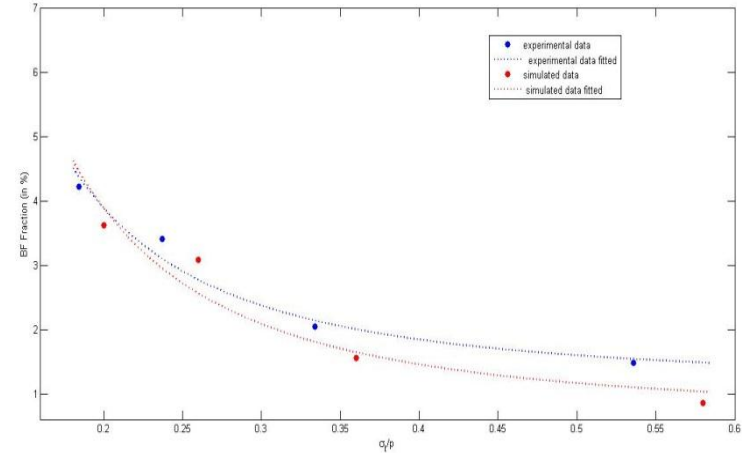


Drift of Secondary Ions (2D picture)

Variation of Backflow fraction at a field ratio of 100 for various values of the ratio σ/p

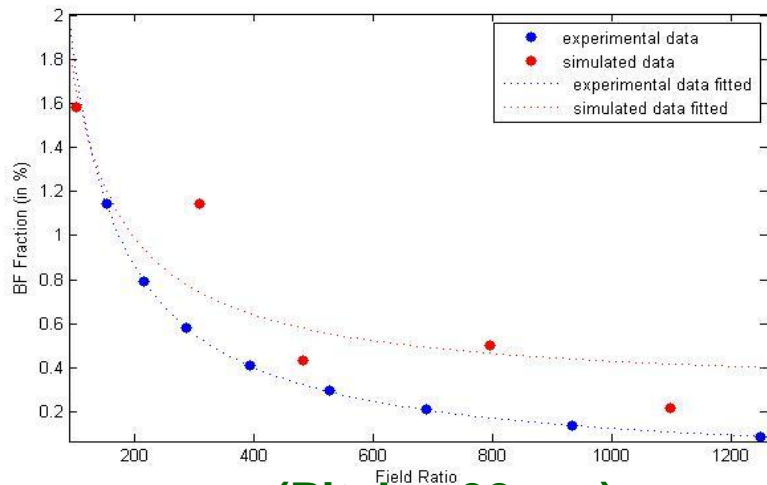


(Amplification gap – 45 μm)

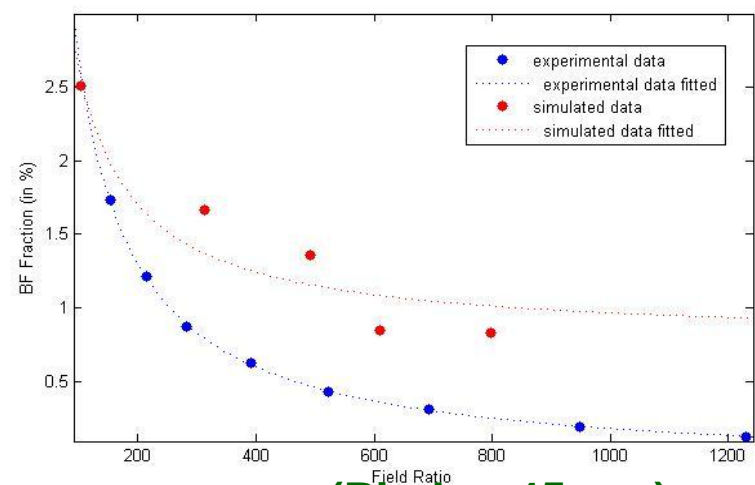


(Amplification gap – 58 μm)

Variation of Backflow fraction with field ratio for 70 μm amplification gap

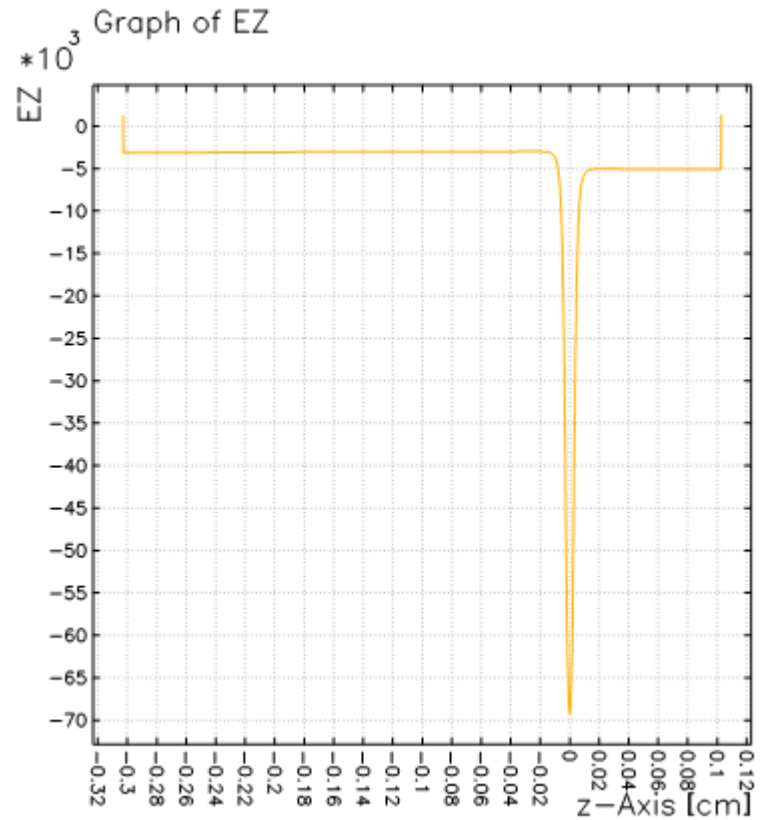
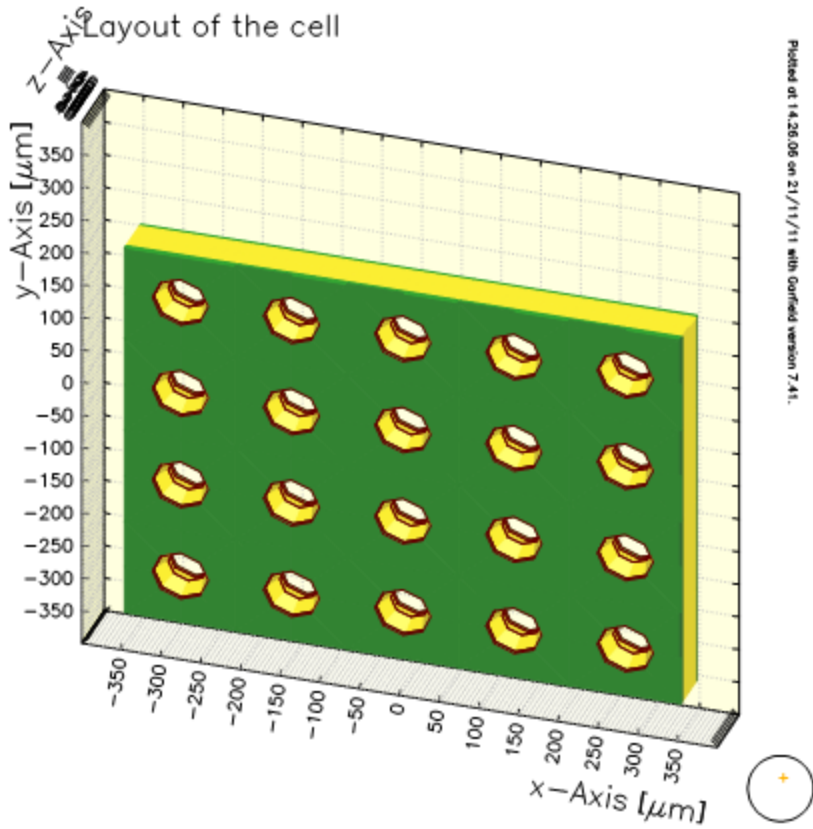


(Pitch – 32 μm)

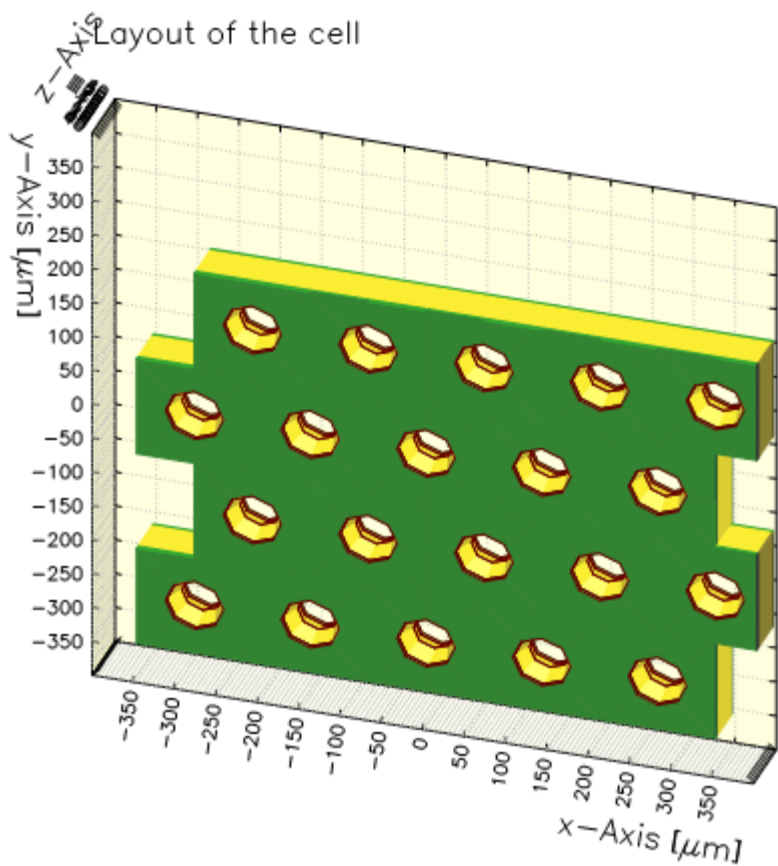


(Pitch – 45 μm)

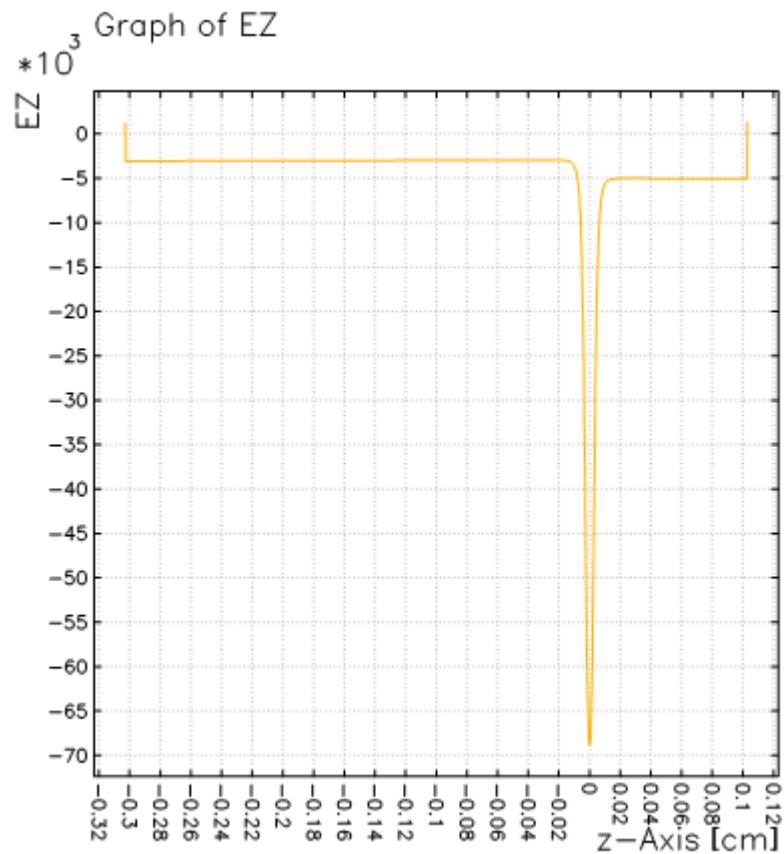
Non-staggered GEM



Staggered GEM with LU

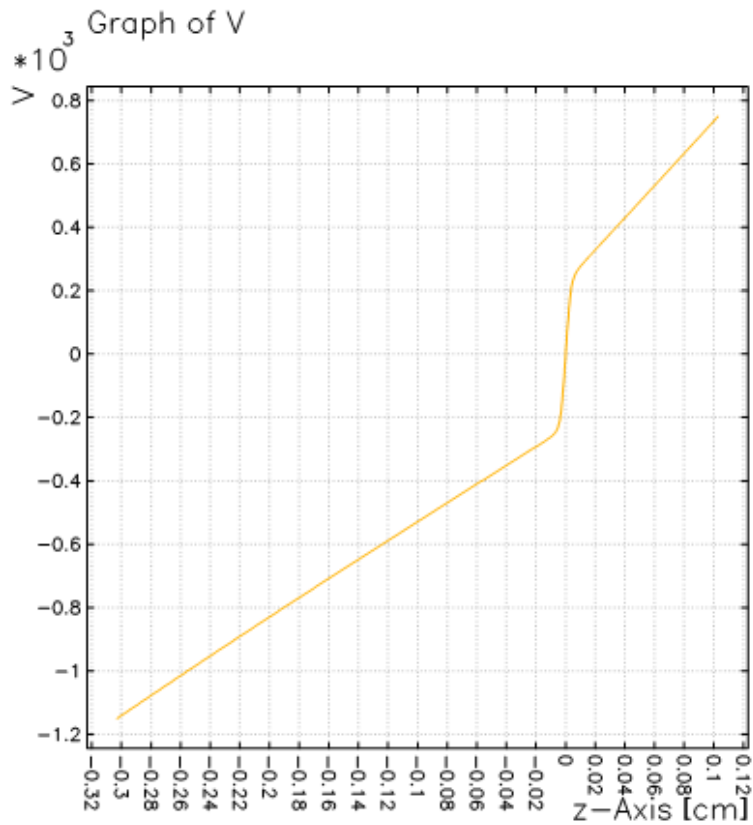


Plotted at 07:57:44 on 22/11/11 with Geant4 version 7.43.

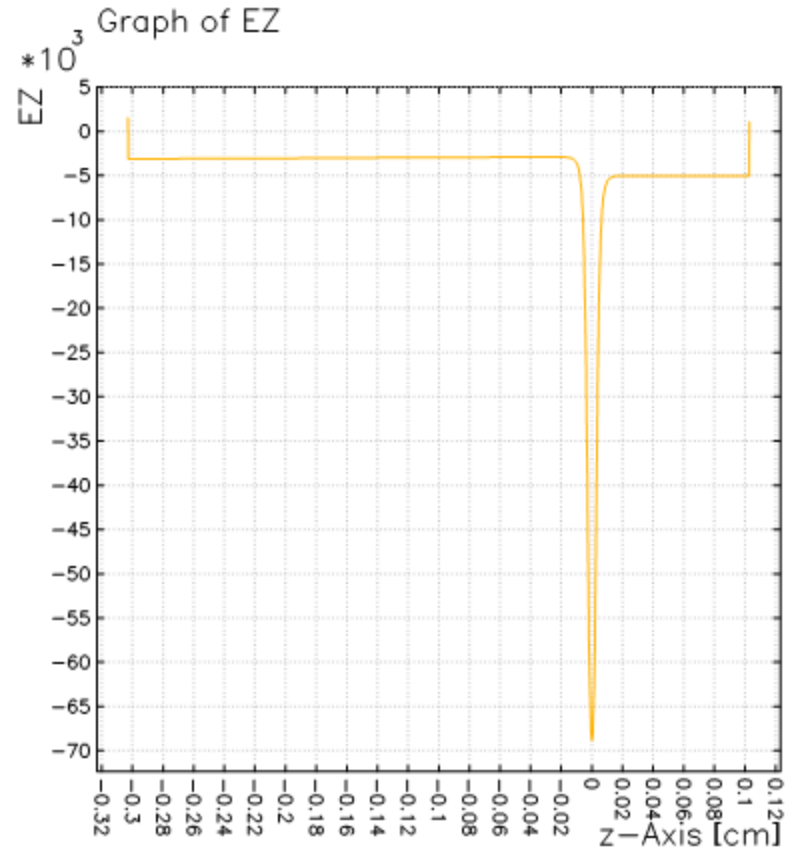


Plotted at 02:53:33 on 22/11/11 with Geant4 version 7.43.

Staggered GEM with SVD

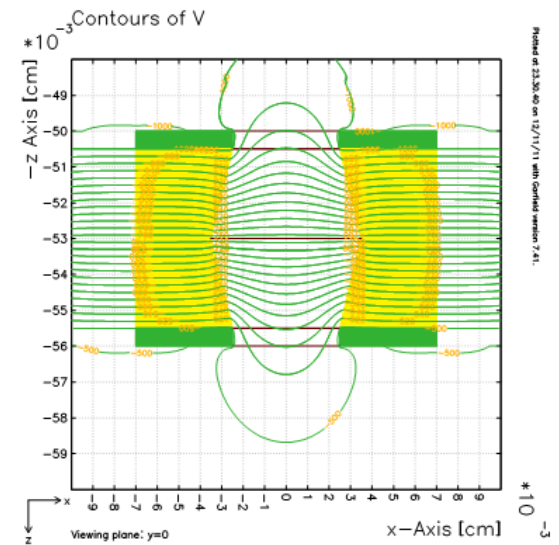
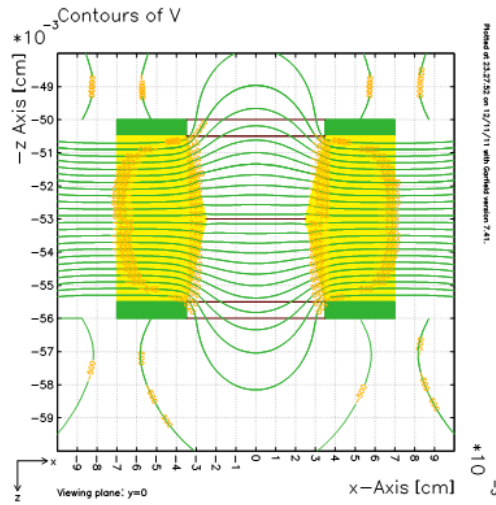
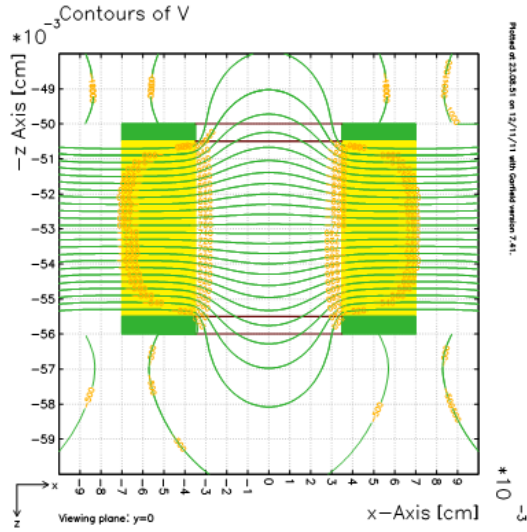


Plotted at 08:06:48 on 22/11/11 with Gnuplot version 7.43.



Plotted at 08:15:54 on 22/11/11 with Gnuplot version 7.43.

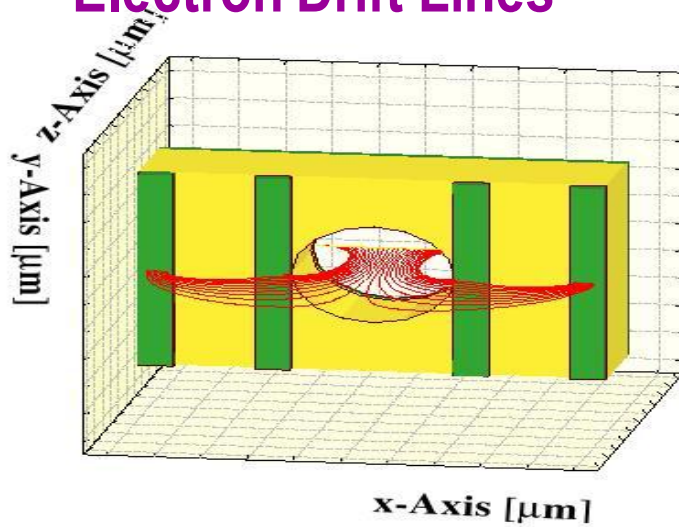
Potential contours in several GEMs



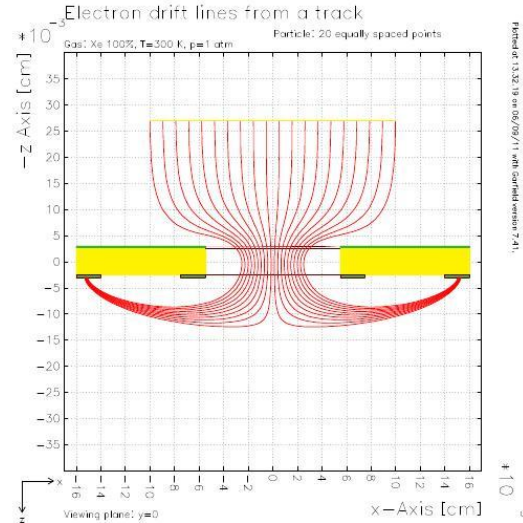
MHSP

efficiency, gain

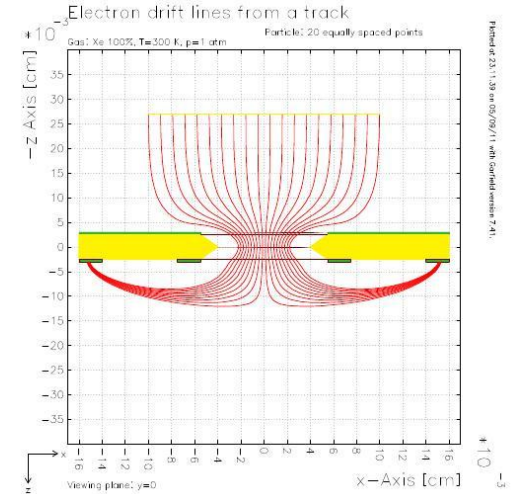
Electron Drift Lines



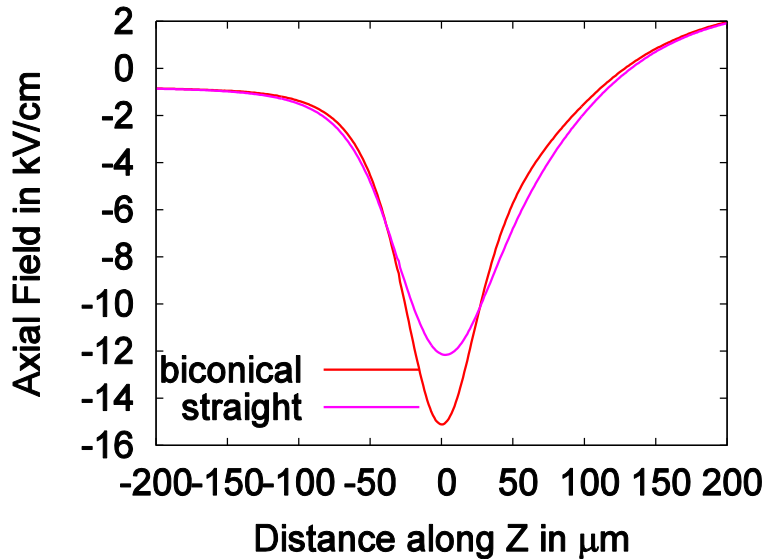
3D Picture



Straight Hole



Bi-conical Hole



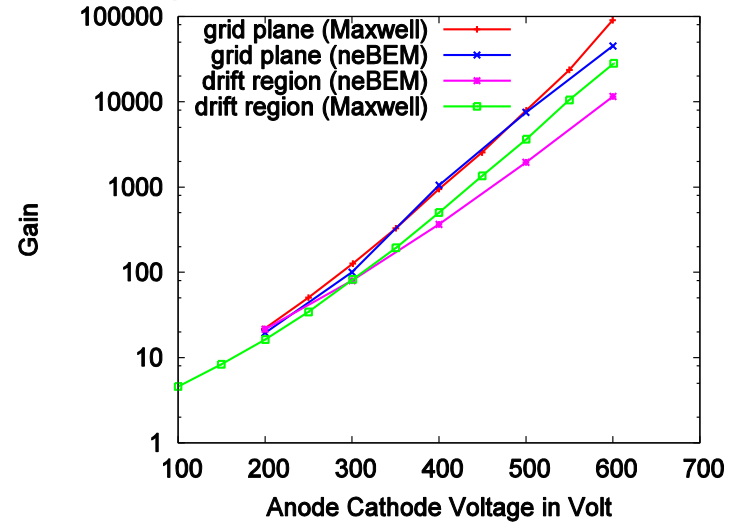
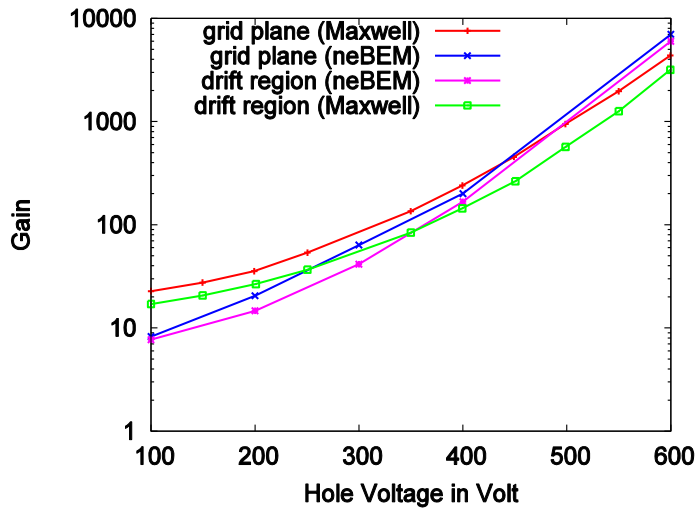
Axial Electric Field

Gas : Pure Xenon Temp.: 300 K, Pressure : 1 Atm

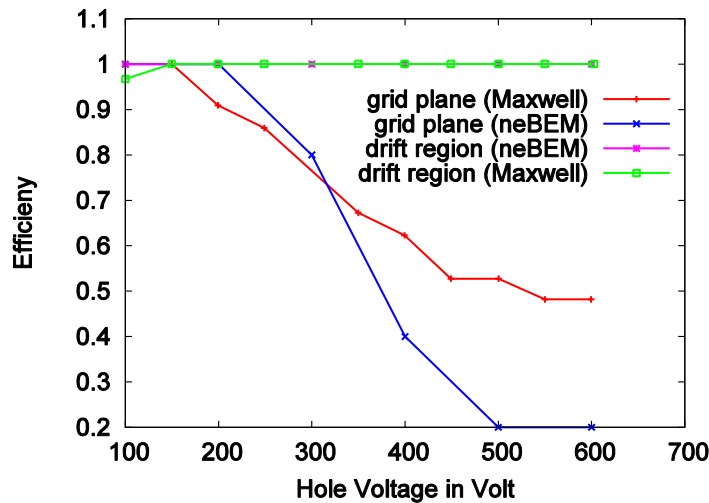
2D Picture

Comparison with existing simulated results (2D calculations using Maxwell)

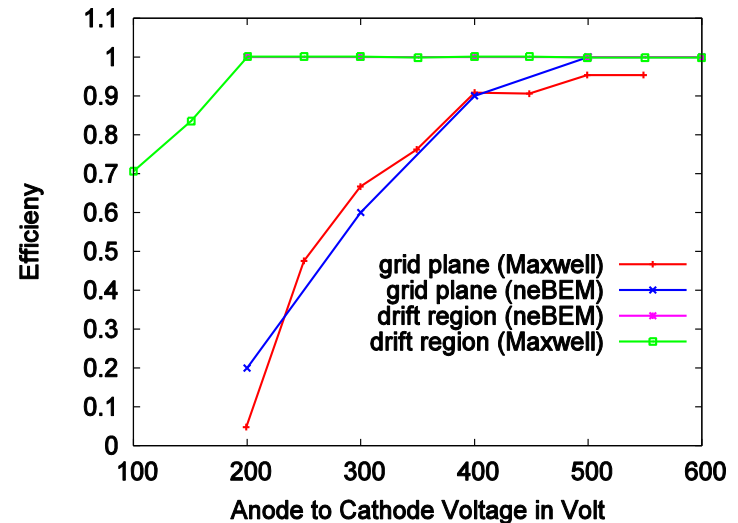
Variation of Total Gain



With Hole Voltage



With Anode to Cathode Voltage



Variation of Electron Collection Efficiency of Anode

Plans for the near-future

Interface to Garfield++

- In the fortran version, neBEM essentially uses the Garfield geometry modeler to set up its model.
- An improved version of the geometry modeler is being developed for Garfield++. As soon as it is there, neBEM will be happily interfaced to the new Garfield++.

Improved geometry modeler, user interface

- Simple enhancements such as mirror repetitions
- Interface to ROOT and Geant 4 geometries; user interfaces based on such and similar programs will immensely help users
- A geometry modeler tuned for neBEM (likely to be based on CGAL or a similar library)

Thank you!